

**Amendments to the Specification**

On page 6 please replace the paragraph after the sub-heading "BRIEF DESCRIPTION OF DRAWINGS" with the following amended paragraphs:

Fig. 1a depicts a prior art device with deposited ohmic metal contacts.

Fig. 1b depicts the prior art device shown in Fig. 1a after exposure to the high temperature.

Fig. 2a depicts a step in a prior art method for forming a GaN device.

Fig. 2b depicts a further processing step for the device shown in Fig. 2a.

Fig. 3a shows a substrate with the plurality of layers and the encapsulation layer.

Fig. 3b shows a substrate with the plurality of layers and the patterned encapsulation layer.

Figs. 3c and 3c-1 shows a further optional step of 3b.

Fig. 3d shows Fig. 3b with the photoresist layer removed.

Fig. 3e shows the refractory metal layer deposited in the opening.

Fig. 3f shows a photoresist layer deposited on the refractory metal layer.

Fig. 3g shows a portion of the refractory metal layer patterned and removed.

Fig. 3h shows a photoresist layer deposited on the refractory metal layer.

Fig. 3i shows a portion of the encapsulation layer and plurality of layers removed.

Fig. 3j shows the deposition of the ohmic metal contacts.

Fig. 3k shows the deposition of the gate metal layer.

Fig. 4a shows a substrate with the plurality of layers of semiconductor material

Fig. 4b shows the photoresist on the second layer, and a portion of the second layer removed.

Fig. 4c shows the deposition of the ohmic metal contacts.

Fig. 4d shows the encapsulation layer deposited on the ohmic metal contacts.

On page 8, please replace the entire first paragraph at the top of the page with the following amended paragraph:

Next, as shown in Figs. 3b-3d, 3b-3c, 3c-1, and 3d, a first opening 108 for a gate structure is formed. First, a first layer of photoresist 106, preferably electron-sensitive photoresist, is deposited

on the exposed SiN layer 104 as shown in Fig. 3b. Electron beam lithography is used to pattern and remove at least a portion of the electron-sensitive photoresist layer 106 and the encapsulation layer 104, thereby creating the first opening 108, as shown in Fig. 3b, which exposes the surface of the second layer 103. Optionally, as shown in Fig. 3c and in even greater detail in Fig. 3c-1, a portion of the second layer 103 may also be removed using reactive ion etching. The removal of a portion of the encapsulation layer 104, leaves two separate encapsulation layers 104a, 104b. The first opening 108 exposes a portion of the second layer 103 and is created by the separation of the encapsulation layers 104a, 104b. After the first opening 108 is created, the remaining portion of the electron-sensitive photoresist layer 106 is removed, as shown in Fig. 3d, using techniques known in the art.

**Amendments to the Drawings**

The attached replacement sheets of the drawings include Figs. 3a-3c, 3c-1, 3d-3k, and 4a-4d. These sheets, which include Figs. 3a-3c, 3c-1, 3d-3k, and 4a-4d, replace the corresponding sheets of drawings originally filed on August 4, 2003.

Attachments: Replacement sheets (6 sheets)